

10V Drive Nch MOSFET

R5009ANJ

●Structure

Silicon N-channel MOSFET

●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) Gate-source voltage (Vgss) guaranteed to be ± 30 V.
- 5) Drive circuits can be simple.
- 6) Parallel use is easy.

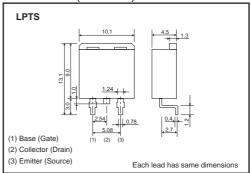
Applications

Switching

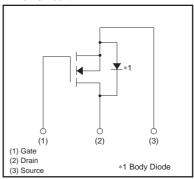
Packaging specifications

	Package	Taping
	Code	TL
Туре	Basic ordering unit (pieces)	1000
R5009	0	

●Dimensions (Unit : mm)



●Inner circuit



● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol		Limits	Unit	
Drain-source voltage	VDSS		500	V	
Gate-source voltage	Vgss		30	V	
Drain augrant	Continuous	ΙD	*3	±9	А
Drain current	Pulsed	IDP	*1	±36	А
Source current	Continuous	ls		9	А
(Body Diode)	Pulsed	Isp *1		36	А
Avalanche Current	las	*2	4.5	А	
Avalanche Energy	Eas	*2	5.4	mJ	
Total power dissipation	Po		50	W	
Channel temperature	Tch		150	°C	
Range of storage tem	Tstg		-55 to +150	°C	

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	2.5	°C/W

^{*1} Pw≤10µs, Duty cycle≤1% *2 L $\stackrel{<}{=}$ 500µH, V $_{D}$ =50V, R $_{G}$ =25 $_{\Omega}$, Starting, Tch=25 $_{C}$ C *3 Limited only by maximum tempterature allowed

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	Igss	-	_	±100	nA	Vgs=±30V, Vps=0V	
Drain-source breakdown voltage	V(BR)DSS	500	_	_	V	ID=1mA, VGS=0V	
Zero gate voltage drain current	IDSS	_	_	100	μΑ	Vps=500V, Vgs=0V	
Gate threshold voltage	VGS(th)	2.5	-	4.5	V	Vos=10V, Io=1mA	
Static drain-source on-state resistance	RDS(on)*	_	0.55	0.72	Ω	Ip=4.5A, Vgs=10V	
Forward transfer admittance	Yfs *	2.5	_	_	S	ID=4.5A, VDS=10V	
Input capacitance	Ciss	_	650	_	pF	Vps=25V	
Output capacitance	Coss	_	400	_	pF	V _G s=0V	
Reverse transfer capacitance	Crss	_	30	_	pF	f=1MHz	
Turn-on delay time	td(on) *	_	30	_	ns	ID=4.5A, VDD≒250V	
Rise time	tr *	_	20	_	ns	Vgs=10V	
Turn-off delay time	td(off) *	_	62	_	ns	RL=55.6Ω	
Fall time	t _f *	_	28	_	ns	R _G =10Ω	
Total gate charge	Qg *	_	21	_	nC	V _{DD} ≒250V	
Gate-source charge	Qgs *	_	5	_	nC	I _D =9A V _G s=10V R _L =27.8Ω / R _G =10Ω	
Gate-drain charge	Q _{gd} *	_	9	_	nC		

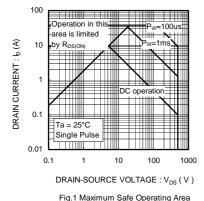
^{*} Pulsed

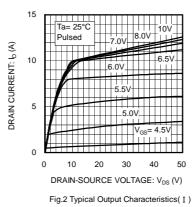
●Body diode characteristics (Source-drain) (Ta=25°C)

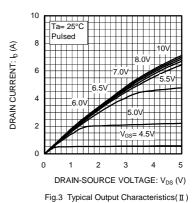
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	_	_	1.5	V	I _S = 9A, V _{GS} =0V

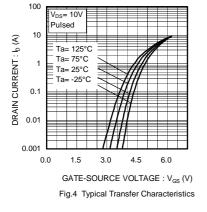
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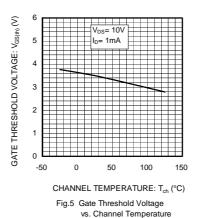
•Electrical characteristics curves

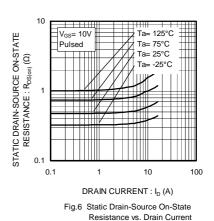












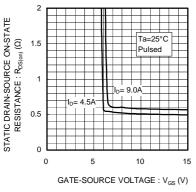


Fig.7 Static Drain-Source On-State Resistance vs. Gate Source Voltage

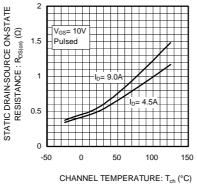


Fig.8 Static Drain-Source On-State
Resistance vs. Channel Temperature

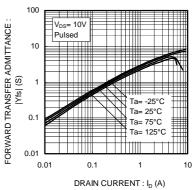
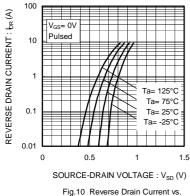
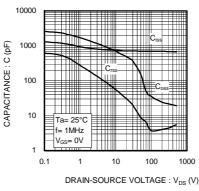
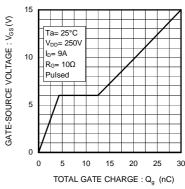


Fig.9 Forward Transfer Admittance vs. Drain Current







Sourse-Drain Voltage

Fig.11 Typical Capacitance vs. Drain-Source Voltage

Fig.12 Dynamic Input Characteristics

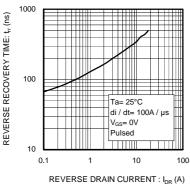


Fig.13 Reverse Recovery Time

vs.Reverse Drain Current

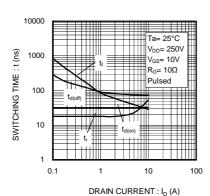


Fig.14 Switching Characteristics

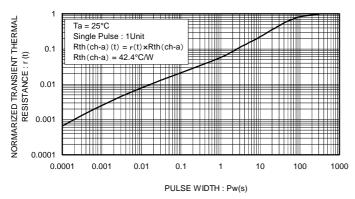


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

R5009ANJ Data Sheet

•Switching characteristics measurement circuit

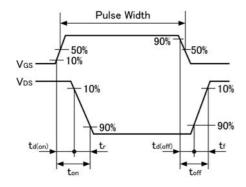


Fig.1-1 Switching time measurement circuit

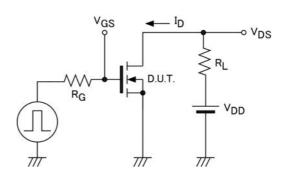


Fig.1-2 Switching waveforms

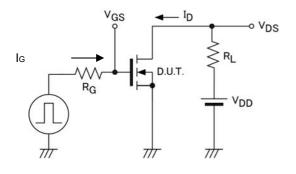


Fig.2-1 Gate charge measurement circuit

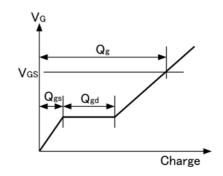


Fig.2-2 Gate charge waveform

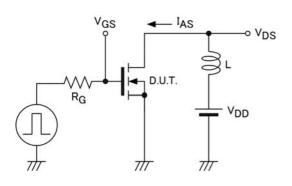


Fig.3-1 Avalanche measurement circuit

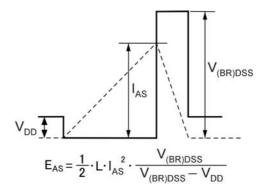


Fig.3-2 Avalanche waveform

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